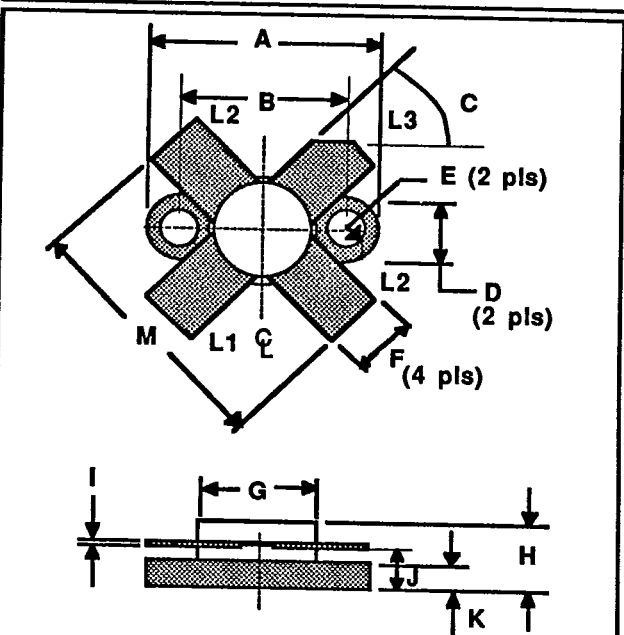


**GENERAL DESCRIPTION**

The S175-50 is a state-of-the-art 50 volt device designed for class A, AB, or C operation in the HF/VHF frequency bands. Its high collector voltage simplifies the design of wideband, SSB, linear amplifiers.

**S175-50**  
**175 WATTS - 50 VOLTS**  
**2-30 MHz**

**HF LINEAR BIPOLAR**



DIM	Millimeter	TOL	Inches	TOL	
L1 : B	A	24.76	.13	.975	.005
L2 : E	B	18.42	.13	.725	.005
L3 : C	C	45°	5°	45°	5°
	D	6.35	.13	.250	.005
	E	3.17 DIA	.13	.125 DIA	.005
	F	5.71	.13	.225	.005
	G	12.70 DIA	.13	.500 DIA	.005
	H	6.65	REF	.262	REF
	I	0.13	.02	.005	.001
	J	4.24	.13	.167	.005
	K	3.17	.13	.125	.005
	M	28.90	.25	1.140	.010

**ABSOLUTE MAXIMUM RATINGS**

Total Power Dissipation @ 25 C Case Temperature (Note 1) **270 W**

Maximum Voltage and Current

BVces Collector to Emitter Voltage **110 V**

BVebo Emitter to Base Voltage **4.0V**

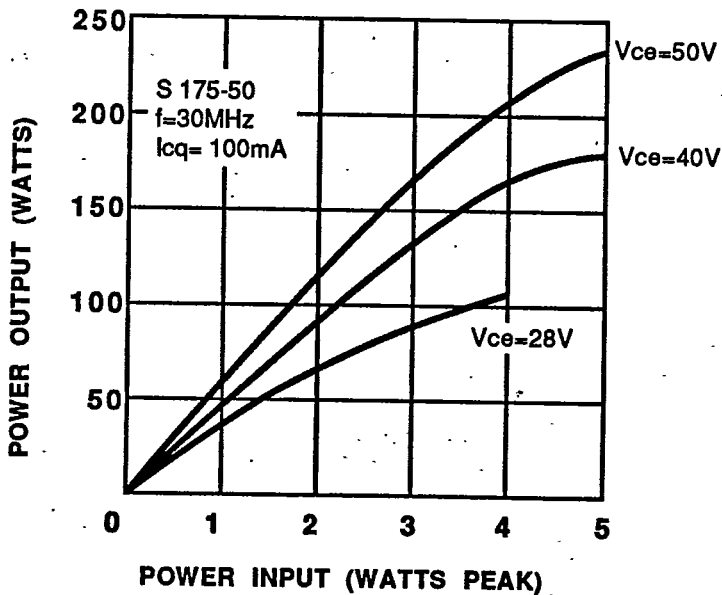
Ic Collector Current **20 A**

Maximum Temperatures

Storage Temperature **-65 to +150°C**

Operating Junction Temperature **+200°C**

**POWER OUTPUT VS POWER INPUT**

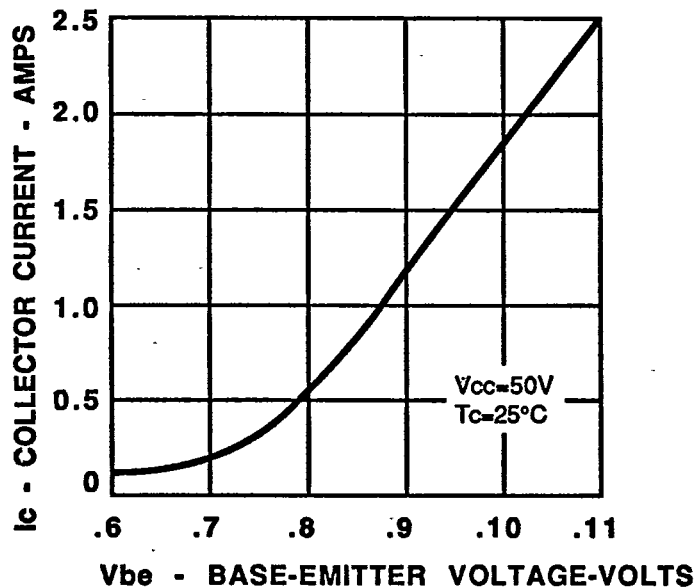


**S175-50-2**

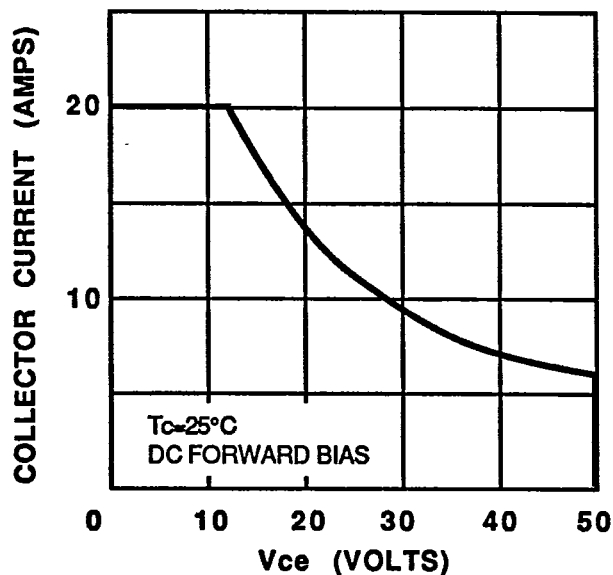
**ELECTRICAL CHARACTERISTICS**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
P <sub>out</sub>	Power Output	f= 30 MHZ, V <sub>cc</sub> = 50 V	175			Watts
P <sub>in</sub>	Power Input	At Rated Power Out			3.5	Watts
P <sub>g</sub>	Power Gain	At Rated Power Out	17			dB
BV <sub>ebo</sub>	Voltage - Emitter to Base	I <sub>e</sub> = 10 mA	4			Volts
BV <sub>ces</sub>	Voltage - Collector to Emitter	I <sub>c</sub> = 100 mA	110			Volts
BV <sub>ceo</sub>	Voltage - Collector to Emitter	I <sub>c</sub> = 100mA	53			Volts
η <sub>c</sub>	Collector Efficiency	At Rated Power Out		65		%
C <sub>ob</sub>	Capacitance-Collector to Base	V <sub>cb</sub> = 50 V, I <sub>e</sub> = 0		180		pF
Z <sub>in</sub>	Series Input Impedance	At Rated Power Out and Frequency		0.6-j0.4		OHMS
Z <sub>l</sub>	Series Load Impedance	At Rated Power Out and Frequency		4.6+j2.1		OHMS
VSWR	Load Mismatch Tolerance	At Rated Power Out			∞:1	
h <sub>FE</sub>	DC - Current Gain	V <sub>ce</sub> = 5V, I <sub>c</sub> =2A	10			

**COLLECTOR CURRENT VS BASE EMITTER VOLTAGE (TYPICAL)**



**DC SAFE OPERATING AREA (TYPICAL)**

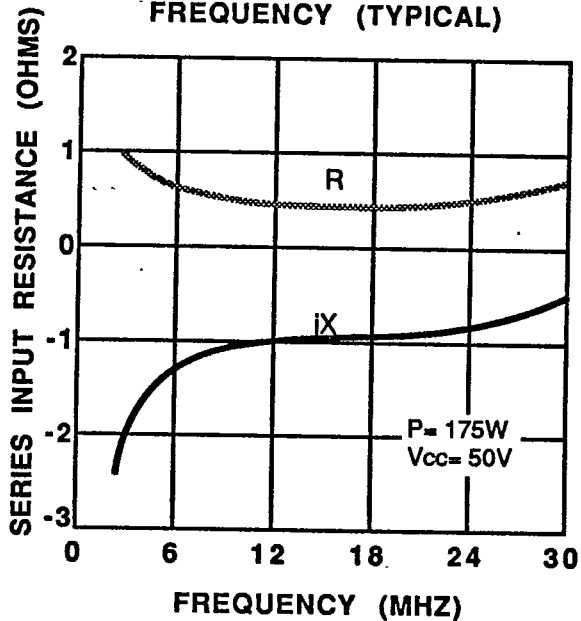


SPECIFICATIONS MAY BE SUBJECT TO CHANGE WITHOUT NOTICE

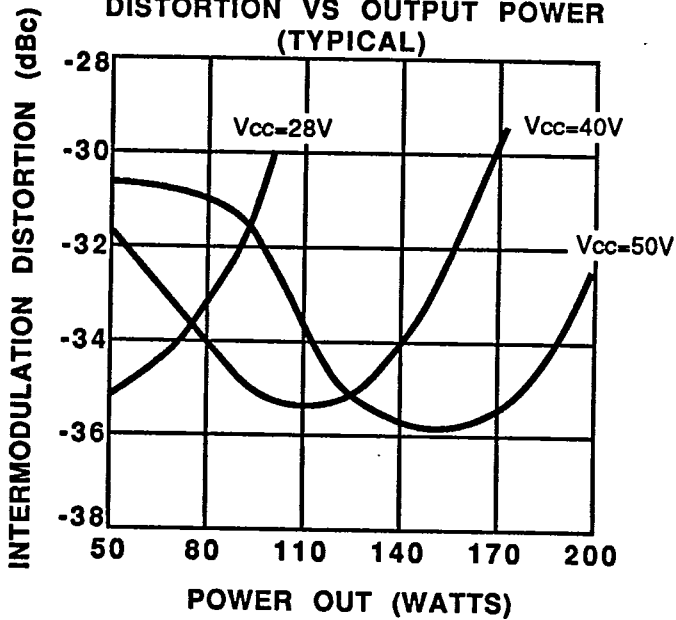
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**S175-50-3**

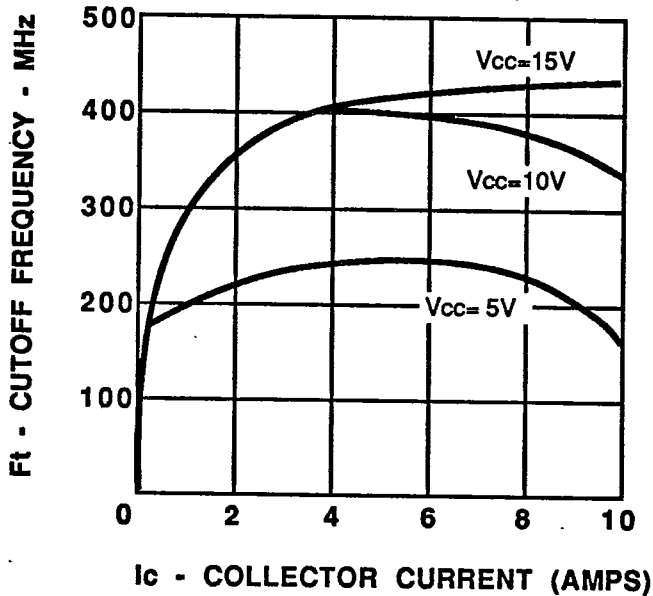
**SERIES INPUT IMPEDANCE VS FREQUENCY (TYPICAL)**



**3RD ORDER INTERMODULATION DISTORTION VS OUTPUT POWER (TYPICAL)**



**CUTOFF FREQUENCY VS. COLLECTOR CURRENT (TYPICAL)**

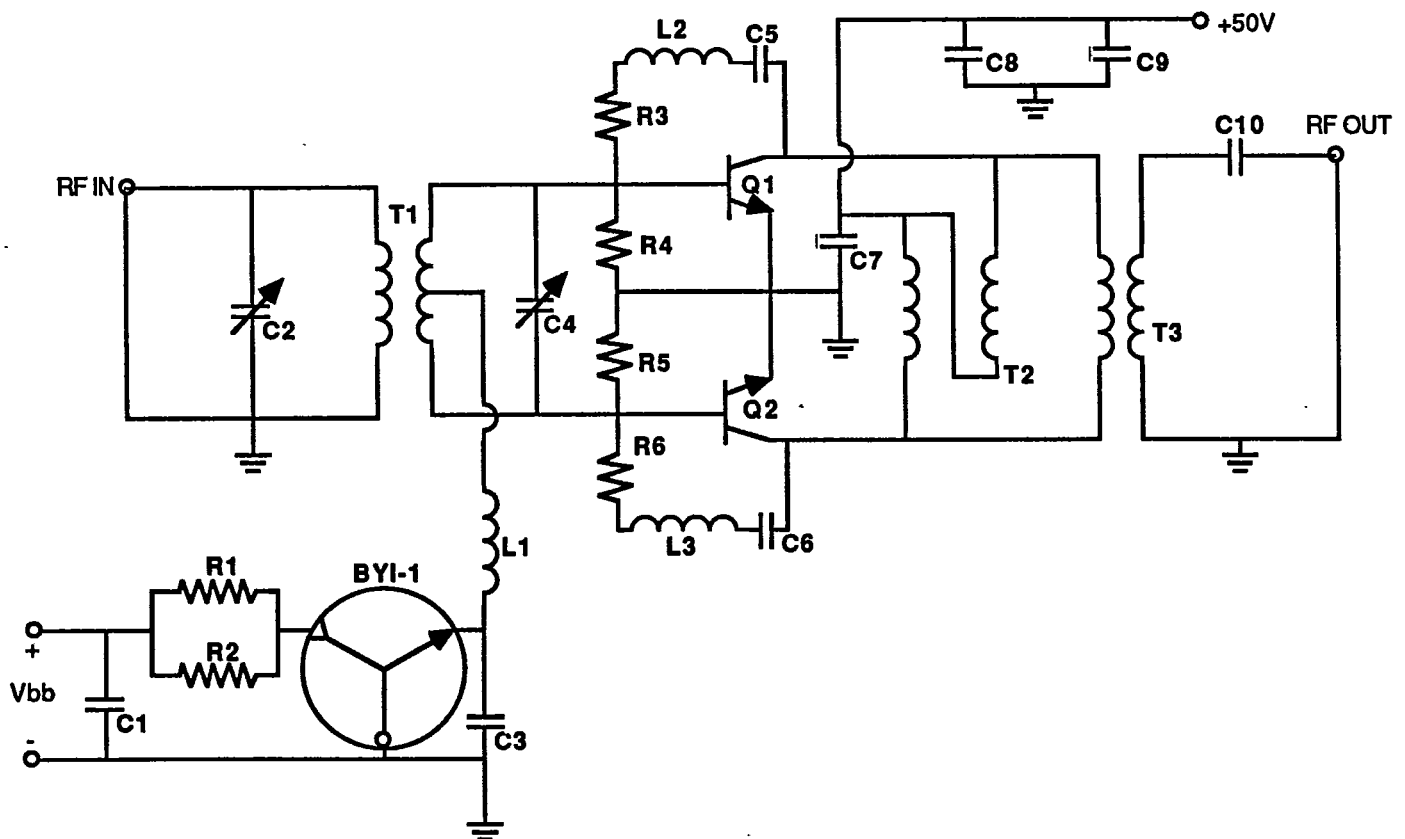


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S175-50-4

## S175-50 TEST CIRCUIT

2-30 MHz, 300 Watts  
Linear Amplifier



Q1, Q1	ACRIAN S175-50
BYISTOR	ACRIAN BYI-1
C1, C3, C5, C6, C7, C8	0.1μF CERAMIC
C2	25-240pF COMPRESSION MICA
C4	75-480pF COMPRESSION MICA
C9	10μF, 50V, ELECTROLYTIC
C10	2700pF DM15
L1	6 TURNS ON INDIANA GENERAL F627-9, H MATERIAL
L2, L3	2.2μH, MOLDED INDUCTOR
R1, R2	22Ω, 2 WATTS
R3, R6	220Ω, 2 WATTS
R4, R5	10Ω, 1/4 WATT

### TRANSFORMER DETAILS

- T1:** 8 BEADS OF INDIANA GENERAL F625-9, H MATERIAL ON TWO BRASS TUBES. THE PRIMARY IS FOUR TURNS OF #20 VINYL CLAD WIRE WOUND THROUGH THE BRASS TUBES.
- T2:** #20 TWISTED PAIR, APPROXIMATELY 2 CRESTS PER CENTIMETER, WOUND ON INDIANA GENERAL F624-19, H MATERIAL
- T3:** 10 BEADS OF INDIANA GENERAL F627-8, H MATERIAL MOUNTED ON TWO BRASS TUBES. THE SECONDARY CONSIST OF 3 #20 VINYL CLAD WIRES IN PARALLEL. THE THREE WIRES SHOULD BE WOUND TO PRODUCE A 2:1 TURNS RATIO.